IN THE CLAIMS

Please amend the claims as follows:

- 1. (original) A method of manufacturing an electronic device comprising a substrate with an electrical element on a first side thereof, the electrical element comprising a first and a second electrode which are connected via metallization to electrical contacts and to electrodes of further electrical elements, the electronic device further comprising a functional element, characterized in that the method comprises the steps of:
- providing a carrier with the functional element, the carrier comprising on the first side an electroconductive patterned layer and on a second side, facing the first side, comprising a carrier layer;
- assembling the substrate and the carrier, the first sides facing each other and the patterned layer being electroconductively connected to the metallization, and
- applying the isolating material between the substrate and the carrier.
- 2. (original) A method as claimed in claim 1, characterized in that inside the carrier a patterned sub-layer is present between the patterned layer and the carrier layer, which patterned layer

and which sub-layer comprise a first and a second pattern, the patterns being mutually distinguished by a recess which has a larger diameter in the plane of the sub-layer than in the plane of the patterned layer thanks to which carrier the patterned layer is embedded in the isolating material upon the application of the isolating material.

- 3. (original) A method as claimed in claim 1, characterized in that the functional element is defined in the patterned layer and in that the carrier layer is removed after the isolating material has been applied.
- 4. (original) A method as claimed in claim 1, characterized in that the patterned layer is connected to the metallization by means of metal or solder balls.
- 5. (currently amended) A method as claimed in claim 1, 2 or 3, characterized in that the patterned layer has a thickness between 1 and 20 $\mu m\,.$
- 6. (currently amended) A method as claimed in claim 1, 2 or 3, characterized in that the patterned layer is bent prior to assembly so that after assembly there is contact between the metallization

and the patterned layer at a first point and in that the functional element is located in a plane substantially parallel to a first side at a predefined distance.

- 7. (original) An electronic device comprising a substrate with an electrical element on its first side which element comprises a first and a second electrode which are connected to a metallization by electrical contacts and electrodes of further electrical elements, the electronic device further comprising an inductive element, characterized in that the inductive element is defined in an electroconductive patterned layer which is located on the first side of the substrate and which is electroconductively connected to the metallization, isolating material being present between said substrate and the patterned layer in which isolating material the patterned layer has been mechanically embedded.
- 8. (original) An electronic device as claimed in claim 7, characterized in that the patterned layer extends in a plane parallel to the first side beyond the substrate and contact pads for external contacting of the electronic device and the isolating material in essence completely envelops the substrate.

- 9. (original) An electronic device as claimed in claim 7, characterized in that the patterned layer is situated between the isolating material and additional layers in which vertical interconnect areas (vias) are defined.
- 10. (original) An electronic device as claimed in claim 7, characterized in that the metallization along a boundary face with the isolating material includes an inductive element which is situated substantially opposite the inductive element in the patterned layer, the inductive elements together forming a strip line.
- 11. (original) An electronic device as claimed in claim 7, characterized in that the substrate comprises a semiconductor material selected from the group of III-V and II-VI connectors and in that the electrical element is a semiconductor element.